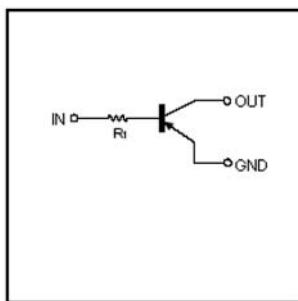


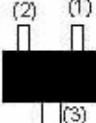
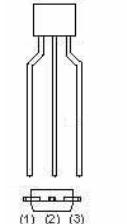
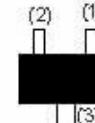
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.

EQUIVALENT CIRCUIT



<u>DTA114TE (SOT-523)</u>	<u>DTA114TUA (SOT-323)</u>
	
1.IN 2.GND 3.OUT	1.IN 2.GND 3.OUT
Addreviated symbol : 94	Addreviated symbol : 94
<u>DTA114TSA (TO-92S)</u>	<u>DTA114TCA (SOT-23)</u>
	
1.GND 2.OUT 3.IN	1.IN 2.GND 3.OUT
(1) (2) (3)	(1) (2) (3)
Addreviated symbol : 94	

ABSOLUTE MAXIMUM RATINGS at ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	LIMITS(DTA114T□)				Unit
		E	UA	CA	SA	
Collector-Base Voltage	V_{CBO}			-50		V
Collector-Emitter Voltage	V_{CEO}			-50		V
Emitter-Base Voltage	V_{EBO}			-5		V
Collector Current-Continuous	I_C			-100		mA
Collector Dissipation	P_C	150		200	300	mW
Junction & Storage temperature	T_J, T_{STG}			150, -55~150		°C

ELECTRICAL CHARACTERISTICS at ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	-50	-	-	V	$I_C = -50\mu\text{A}, I_E = 0$
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-50	-	-		$I_C = -1\text{mA}, I_B = 0$
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	-5	-	-	V	$I_E = -50\mu\text{A}, I_C = 0$
Collector cut-off current	I_{CBO}	-	-	-0.5	μA	$V_{\text{CB}} = -50\text{V}, I_E = 0$
Emitter cut-off current	I_{EBO}	-	-	-0.5	μA	$V_{\text{EB}} = -4\text{V}, I_C = 0$
DC current gain	h_{FE}	100	250	600		$V_{\text{CE}} = -5\text{V}, I_C = -1\text{mA}$
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	-	-	-0.3	V	$I_C = -10\text{mA}, I_B = -1\text{mA}$
Transition frequency	f_T	-	250	-	MHz	$V_{\text{CE}} = -10\text{V}, I_C = -5\text{mA}, f = 100\text{MHz}$
Input resistor	R1	7	10	13	kΩ	

CHARACTERISTIC CURVES

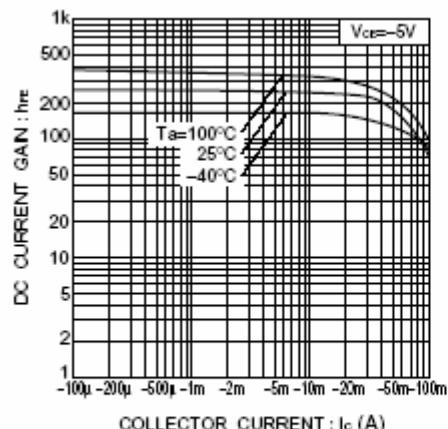


Fig.1 DC current gain vs. collector current

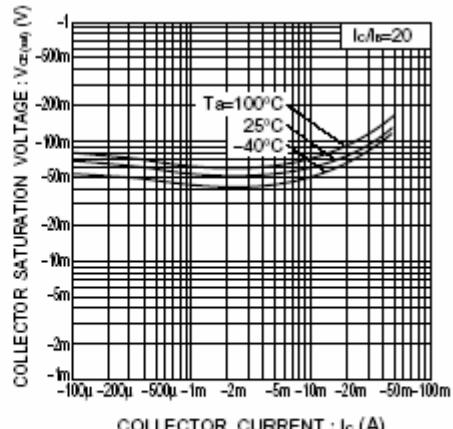


Fig.2 Collector-emitter saturation voltage vs. collector current